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INFORMATION DISCLOSURE CITATION PAGE 1 OF 2				Atty Docket No. OPE-002		Serial No. 09/556,285	
				Applicant G. Taylor			
				Filed April 24, 2000		Group 2811	
US PATENT DOCUMENTS							
Examiner Initials		Document No.	Date	Name	Class	Subclass	Filing date if approp.
	A	4,688,484	07/28/1987	Derkite, Jr.	357	16	
<i>SMH</i>	B	6,351,001	02/26/2002	Stevens et al.	257	223	
	C						
	D						
	E						
	F						
	G						
	H						
	I						
	J						
	K						
FOREIGN PATENT DOCUMENTS							
Examiner Initials		Document No.	Date	Country	Class	Subclass	Translation Yes No
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							
<i>SMH</i>	1	Gunapala et al., "Quantum Well Infrared Photodetector (QWIP) Focal Plane Arrays," Semiconductors and Semimetals series, Vol. 62, 1999					
<i>SMH</i>	2	Song et al., "A Resistive-Gate Al _{0.3} Ga _{0.7} As/GaAs 2DEG CCD with High Charge-Transfer Efficiency at 1 GHz," IEEE Trans. On Elec. Dev., Vol. 38, No. 4, April 1991, pp. 930-932					
<i>SMH</i>	3	Bakker et al., "The Tacking CCD: A New CCD Concept," IEEE Trans. On Elec. Dev., Vol. 38, No. 5, May 1991, pp. 1193-1200					
EXAMINER <i>G. Munson</i>				DATE CONSIDERED <i>22 MARCH 2004</i>			



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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)				
<i>LNH</i>	4	Ula et al., "Simulation, Design, and Fabrication of Thin-Film Resistive-gate GaAs Charge Coupled Devices," IEEE Electron Devices Meeting, 1990. Technical Digest International, December 1990, pp. 271-274		
	5	Davidson et al., "GaAs charge-coupled devices," Can. J. Phys., Vol. 67, 1989, pp. 225-231		
	6	Song et al., "Characterization of Evaporated Cr-SiO Cermet Films for Resistive-Gate CCD Applications," IEEE Trans. On Elec. Dev., Vol. 36, No. 9, Sept. 1989, pp. 1575-1579		
	7	LeNoble et al., "A Two-Phase GaAs Cermet Gate Charge-Coupled Device," IEEE Trans. On Elec. Dev., Vol. 37, No. 8, Aug. 1990, pp. 1796-1799		
	8	Beggs et al., "Optical charge injection into a gallium arsenide acoustic charge transport device," J. Appl. Phys., Vol. 63, No. 7, April 1988, pp. 2425-2430		
	9	Ablassmeier et al., "Three-Phase GaAs Schottky-Barrier CCD Operated up to 100-MHz Clock Frequency," IEEE Trans. On Elec. Dev., Vol. 27, No. 6, June 1980, pp. 1181-1183		
	10	LeNoble et al., "Uniphase operation of a GaAs resistive gate charge-coupled device," Can. J. Phys. Vol. 70, 1992, pp. 1143-1147		
	11	LeNoble et al., "Two-phase GaAs cermet-gate charge-coupled devices," Can. J. Phys., Vol. 69, 1991, pp. 224-227		
	12	Ula et al., "Optimization of Thin-Film Resistive-Gate and Capacitive-Gate GaAs Charge-Coupled Devices," IEEE Trans. On Elec. Dev., Vol. 39, No. 5, May 1992, pp. 1032-1040		
	<i>LNH</i>	13	LeNoble et al., "The Surface Potential Variation in the Interference Gaps of GaAs Cermet-Gate Charge-Coupled Devices," Solid-State Electronics, Vol. 33, No. 7, 1990, pp. 851-857	
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